SOT23 NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

FMMT489

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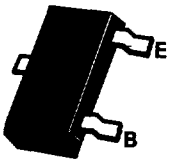
FEATURES

* Very low equivalent on-resistance; $R_{CE(sat)}$ 175mΩ at 1A



COMPLEMENTARY TYPE – FMMT589
PARTMARKING DETAIL – 489

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	4	A
Base Current	I_B	200	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	50		V	I_C=100μA
	$V_{CEO(sus)}$	30		V	I_C=10mA*
	$V_{(BR)EBO}$	5		V	I_E=100μA
Collector Cut-Off Current	I_{CBO}		100	nA	V_{CB}=30V
	I_{CES}		100	nA	V_{CES}=30V
Emitter Cut-Off Current	I_{EBO}		100	nA	V_{EB}=4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.3 0.6	V V	I_C=1A, I_B=100mA* I_C=2A, I_B=200mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.1	V	I_C=1A, I_B=100mA*
Base-Emitter Turn On Voltage	$V_{BE(on)}$		1.0	V	I_C=1A, V_{CE}=2V*
Static Forward Current Transfer Ratio	h_{FE}	100 100 60 20	300		I_C=1mA, V_{CE}=2V* I_C=1A, V_{CE}=2V* I_C=2A, V_{CE}=2V* I_C=4A, V_{CE}=2V*
Transition Frequency	f_T	150		MHz	I_C=50mA, V_{CE}=10V f=100MHz
Collector-Base Breakdown Voltage	C_{obo}		10	pF	V_{CB}=10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%
For typical characteristics graphs see FMMT449 datasheet